

8inch Optical SiC Substrate

GZSC 200mm Optical Sic Substrate Specification				
Parameter	Unit	Specification Value		Remark
Grade		Production Grade	Dummy Grade	
Diameter	mm	200.0 mm±0.25 mm		
Thickness	μm	500.0 μm ±25.0 μm		
Primary Flat		Notch		
Primary Flat Length	mm	32.5±2.0		
Micropipe Density	cm ²	≤ 0.1	≤ 5	
TTV	μm	≤ 2	≤ 10	
Bow (absolute value)	μm	≤ 15	≤ 30	
Warp	μm	≤ 25	≤ 40	
LTV (max, 10mm×10mm)	μm	≤ 1	NA	
Surface Finish		Double side polish, Si epi-face CMP, C face CMP		
Surface Roughness	nm	Si Face Ra≤ 0.5 nm and C Face Ra≤ 0.5 nm		
Edge Chips (No EE)		None permitted	None greater than 0.5 mm depth.	
Laser marking		As per SEMI Standard		
Polytype Area by polarized light		None	Cumulative area < 30%	
Hex Plates by high-intensity light		None	Cumulative area < 5%	
Cracks by high-intensity light		None permitted		
Scratches by high-intensity light		≤1×Diameter	NA	
Area Contamination by high-intensity light		None permitted	NA	
Packaging		Multi-wafer cassette or Single Wafer Container Inner packing: vacuum, outer packing: no damage, no air leakage		